

Product Specification PE42672 DIE

SP7T UltraCMOS[™] 2.75 V Switch 100 – 3000 MHz, +67 dBm IIP3

Figure 1. Functional Diagram

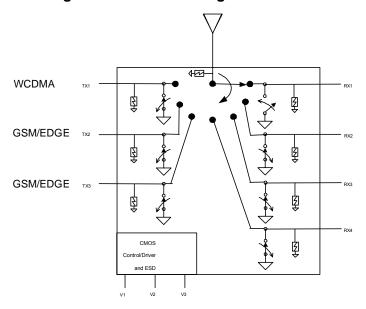
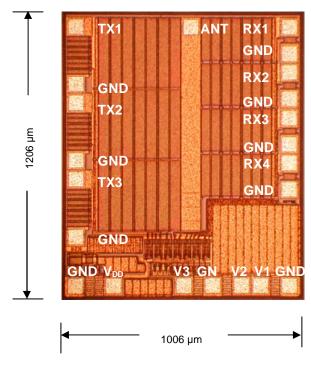


Figure 2. Die Top View*



^{*} Dimensions shown are drawn die size.

Features

- Dedicated TX1 port for WCDMA, TX2 and TX3 ports for GSM/EDGE
- Three pin CMOS logic control with integral decoder/driver
- Exceptional harmonic performance:
 2f_o = -85 dBc and 3f_o = -78.5 dBc
- Low TX insertion loss: 0.60 dB at 900 MHz, 0.70 dB at 1900 MHz
- TX RX Isolation of 44 dB at 900 MHz, 38 dB at 1900 MHz
- 1000 V HBM ESD tolerance RF ports
- +67 dBm IIP3
- -109 dBm IMD3
- No blocking capacitors required

Product Description

The PE42672 is a HaRP™-enhanced SP7T RF Switch developed on the UltraCMOS™ process technology. It addresses the specific design needs of the Quad-Band GSM Handset Antenna Switch Module Market for use in GSM/EDGE/PCS/DCS/WCDMA handsets. The switch is comprised of three TX ports and four RX ports. TX1 is designed for WCDMA and TX2 and TX3 are designed for GSM/ EDGE. The four symmetric RX ports can be used for GSM/EDGE/PCS RX. On-chip CMOS decoder logic facilitates three-pin low voltage CMOS control, while high ESD tolerance of 1000 V at RF ports, no blocking capacitor requirements, and on-chip SAW filter overvoltage protection devices make this the ultimate in integration and ruggedness.

Peregrine's HaRP™ technology enhancements deliver high linearity and exceptional harmonics performance. It is an innovative feature of the UltraCMOS™ process, providing performance superior to GaAs with the economy and integration of conventional CMOS.

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Table 1. Target Electrical Specifications @ 25 °C, V_{DD} = 2.75 V

| Parameter | Condition | | Units |
|-----------------------------|--|----------------------------------|----------------------------|
| Insertion loss ¹ | TX - Ant (850 / 900) TX - Ant (1800 / 1900) TX - Ant (2100 WCDMA) RX - Ant (850 / 900) RX - Ant (1800 / 1900) | 0.6 0.7 0.75 0.9 0.9 | dB dB dB dB dB |
| Return Loss | Port under test in on state | 20 | dB |
| Isolation | TX - RX (850 / 900) TX - RX (1800 / 1900) TX - TX (850 / 900) TX - TX (1800 / 1900) TX1 - RX (1900 / 2100) | 44 38 29 23 39 | dB dB dB dB dB |
| 2nd Harmonic | TX 850 / 900 MHz, +35 dBm output power, 50 Ω TX 1800 / 1900 MHz, +33 dBm output power, 50 Ω | -85 -84 | dBc dBc |
| 3rd Harmonic | TX 850 / 900 MHz, +35 dBm output power, 50 Ω TX 1800 / 1900 MHz, +33 dBm output power, 50 Ω | -78.5 -78.5 | dBc dBc |
| IMD3 distortion at 2.14 GHz | TX1 Measured at 2.14 GHz at Ant port, input +20 dBm CW signal at 1.95 GHz and -15 dBm CW signal at 1.76 GHz | | dBm |
| WCDMA 2100 IIP3 | TX1 Measured at 2.14 GHz at Ant port, input +20 dBm CW signal at 1.95 GHz and -15 dBm CW signal at 1.76 GHz | | dBm |
| Switching time | (10-90%) (90-10%) RF | 2 | μs |

Note: 1. Insertion loss specified with optimal impedance matching.

Table 2. Operating Ranges

| Parameter | Symbol | Min | Тур | Max | Units |
|---|-----------------|------|------|------|-------|
| Temperature range | T _{OP} | -40 | | +85 | °C |
| V _{DD} Supply Voltage | V_{DD} | 2.65 | 2.75 | 2.85 | V |
| I_{DD} Power Supply Current $(V_{DD} = 2.75 \text{ V})$ | I _{DD} | | 13 | 50 | μΑ |
| TX input power² (VSWR ≤ 3:1) 824-915 MHz | | | | +35 | -ID |
| TX input power² (VSWR ≤ 3:1) 1710-1910 MHz | P _{IN} | | | +33 | dBm |
| RX input power² (VSWR =1:1) | P _{IN} | | | +20 | dBm |
| Control Voltage High | V _{IH} | 1.4 | | | V |
| Control Voltage Low | V _{IL} | | | 0.4 | V |

Note: 2. Assumes RF input period of 4620 μ s and duty cycle of 50%.

Table 3. Absolute Maximum Ratings

| Symbol | Parameter/Conditions | Min | Max | Units | |
|-------------------------------|--|------|-----------------------|----------|--|
| V_{DD} | Power supply voltage | -0.3 | 4.0 | V | |
| Vı | Voltage on any input | -0.3 | V _{DD} + 0.3 | V | |
| T _{ST} | Storage temperature range -65 | | +150 | °C | |
| | TX input power (50 Ω) ^{3,4} 824-915 MHz | | +38 | | |
| P _{IN} (50 Ω) | TX input power (50 Ω) ^{3,4} 1710-1910 MHz | | +36 | dBm | |
| | RX input power (50 Ω) 3,4 | | +23 | | |
| D (1114) | TX input power (VSWR = (∞:1) ^{3,4} 824-915 MHz | | +35 | -ID | |
| P _{IN} (∞:1) | TX input power (VSWR = (∞:1) ^{3,4} 1710-1910 MHz | | +33 | dBm 3 | |
| V _{ESD} ⁵ | ESD Voltage, Digital Pins | | 500 | V | |
| | ESD Voltage, RF Pins | | 1000 | V | |

Note: 3. Assumes RF input period of 4620 µs and duty cycle of 50%.

Part performance is not guaranteed under these conditions. Exposure to absolute maximum conditions for extended periods of time may adversely affect reliability. Stresses in excess of absolute maximum ratings may cause permanent damage.

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^{4.} V_{DD} within operating range specified in Table 2.

^{5.} ESD Voltage (HBM, ML_STD 883 Method 3015.7)



Table 4. Pin Descriptions

| Pin No. | Pin Name | Description | |
|---------|------------------|--|--|
| 1 | ANT | RF Common – Antenna | |
| 2 | TX1 ⁷ | RF I/O - TX1 | |
| 3 | GND ⁶ | Ground | |
| 4 | TX2 ⁷ | RF I/O – TX2 | |
| 5 | GND ⁶ | Ground | |
| 6 | TX3 | RF I/O – TX3 | |
| 7 | GND ⁶ | Ground | |
| 8 | GND ⁶ | Ground | |
| 9 | V_{DD} | Supply | |
| 10 | V3 | Switch control input, CMOS logic level | |
| 11 | GND ⁶ | Ground | |
| 12 | V2 | Switch control input, CMOS logic level | |
| 13 | V1 | Switch control input, CMOS logic level | |
| 14 | GND ⁶ | Ground | |
| 15 | GND ⁶ | Ground | |
| 16 | RX4 ⁷ | RF I/O – RX4 | |
| 17 | GND ⁶ | Ground | |
| 18 | RX3 ⁷ | RF I/O – RX3 | |
| 19 | GND ⁶ | Ground | |
| 20 | RX2 ⁷ | RF I/O – RX2 | |
| 21 | GND ⁶ | Ground | |
| 22 | RX1 ⁷ | RF I/O – RX1 | |

Notes: 6. Bond wires should be physically short and connected to ground plane for best performance.

Figure 3. Pad Configuration (Top View)

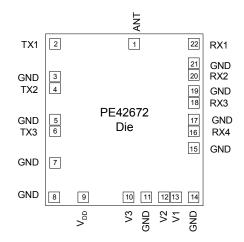


Table 5. Truth Table

| Path | V3 | V2 | V1 |
|-----------|----|----|----|
| RX1 - ANT | 0 | 0 | 0 |
| RX2 - ANT | 0 | 0 | 1 |
| RX3 - ANT | 0 | 1 | 0 |
| RX4 - ANT | 0 | 1 | 1 |
| TX1 - ANT | 1 | 0 | 0 |
| TX2 - ANT | 1 | 0 | 1 |
| TX3 - ANT | 1 | 1 | 0 |
| All Off | 1 | 1 | 1 |

Electrostatic Discharge (ESD) Precautions

When handling this UltraCMOS™ device, observe the same precautions that you would use with other ESD-sensitive devices. Although this device contains circuitry to protect it from damage due to ESD, precautions should be taken to avoid exceeding the specified rating.

Latch-Up Avoidance

Unlike conventional CMOS devices, UltraCMOS™ devices are immune to latch-up.

Table 6. Ordering Information

| Order Code | Description | Package | Shipping Method |
|------------|------------------|----------------|------------------------------------|
| 42672-90 | PE42672-DIE-D | Film Frame | Wafer (Gross Die / Wafer Quantity) |
| 42672-99 | PE42672-DIE-400G | Waffle Pack | 400 Dice / Waffle Pack |
| 42672-00 | PE42672-DIE-1H | Evaluation Kit | 1/ box |

^{7.} Blocking capacitors needed only when non-zero DC voltage present.



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Data Sheet Identification

Advance Information

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The product is in a formative or design stage. The data sheet contains design target specifications for product development. Specifications and features may change in any manner without notice.

Preliminary Specification

The data sheet contains preliminary data. Additional data may be added at a later date. Peregrine reserves the right to change specifications at any time without notice in order to supply the best possible product.

Product Specification

The data sheet contains final data. In the event Peregrine decides to change the specifications, Peregrine will notify customers of the intended changes by issuing a DCN (Document Change Notice).

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